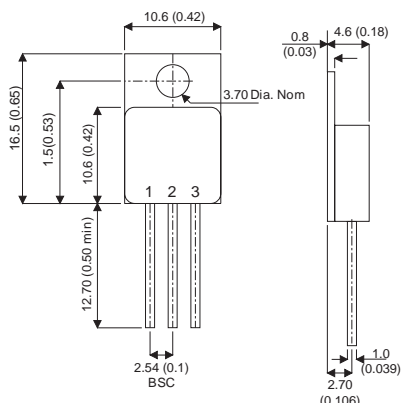


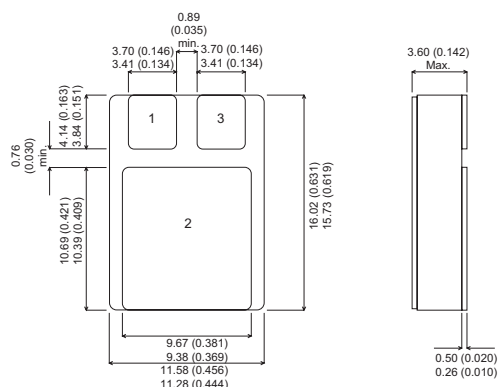
SILICON PNP EPITAXIAL BASE IN TO220 METAL AND CERAMIC SURFACE MOUNT PACKAGES

MECHANICAL DATA

Dimensions in mm(inches)



TO220M - TO220 Metal Package - Isolated (TO-257AB)



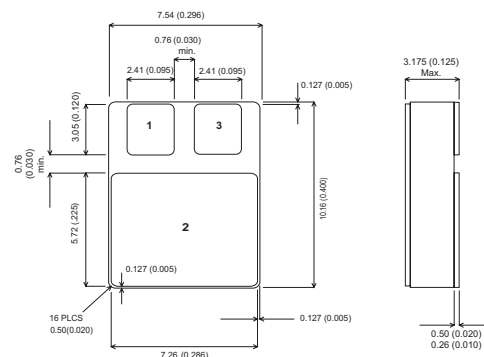
SMD1 - Ceramic Surface Mount Package (TO-276AB)

FEATURES

- HERMETIC METAL OR CERAMIC PACKAGES
- HIGH RELIABILITY
- MILITARY AND SPACE OPTIONS
- SCREENING TO CECC LEVELS
- FULLY ISOLATED (METAL VERSION)

APPLICATIONS

- POWER LINEAR AND SWITCHING APPLICATIONS
- GENERAL PURPOSE POWER



SMD05 - Ceramic Surface Mount Package (TO-276AA)

Pin 1 – Base Pin 2 – Collector Pin 3 – Emitter

ABSOLUTE MAXIMUM RATINGS ($T_{case}=25^{\circ}C$ unless otherwise stated)

		BDS13	BDS14	BDS15
V_{CBO}	Collector - Base voltage ($I_E = 0$)	- 60V	- 80V	- 100V
V_{CEO}	Collector - Emitter voltage ($I_B = 0$)	- 60V	- 80V	- 100V
V_{EBO}	Emitter - Base voltage ($I_C = 0$)		- 5V	
I_E, I_C	Emitter , Collector current		- 15A	
I_B	Base current		- 5A	
P_{tot}	Total power dissipation at $T_{case} \leq 25^{\circ}C$		90W	
T_{stg}	Storage Temperature		-65 to 200°C	
T_j	Junction Temperature		200°C	

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CBO} Collector cut-off current (I _E = 0)	BDS13 V _{CB} = - 60V			- 500	μA
	BDS14 V _{CB} = - 80V			- 500	
	BDS15 V _{CB} = - 100V			- 500	
I _{CEO} Collector cut-off current (I _B = 0)	BDS13 V _{CE} = - 30V			- 1	mA
	BDS14 V _{CE} = - 40V			- 1	
	BDS15 V _{CE} = - 50V			- 1	
I _{EBO} Emitter cut-off current (I _C = 0)	V _{EB} = - 5V			- 1	mA
V _{CEO(sus)*} Collector - Emitter sustaining voltage (I _B = 0)	BDS13 BDS14 I _C = - 100mA BDS15	- 60 - 80 - 100			V
V _{CE(sat)*} Collector - Emitter saturation voltage	I _C = - 5A I _B = - 0.5A			- 1	V
	I _C = - 10A I _B = - 2.5A			- 3	
V _{BE(sat)*} Base - Emitter saturation voltage	I _C = - 10A I _B = - 2.5A			- 2.5	V
V _{BE*} Base - Emitter voltage	I _C = - 5A V _{CE} = - 4V			- 1.5	V
h _{FE*} DC Current Gain	I _C = - 0.5A V _{CE} = - 4V	40		300	
	I _C = - 5A V _{CE} = - 4V	15		150	
	I _C = - 10A V _{CE} = - 4V	5			
f _T Transition frequency	I _C = - 0.5A V _{CE} = - 4V f = 1MHz	3			MHz

*Pulsed : Pulse duration = 300 μs , duty cycle = 1.5%

SWITCHING CHARACTERISTICS

Parameter	Test Conditions	Max.	Unit
t _{on} On Time (t _d + t _r)	I _C = - 4A V _{CC} = - 30V I _{B1} = - 0.4A	0.7	μs
t _s Storage Time	I _C = - 4A V _{CC} = - 30V	1.0	μs
t _f Fall Time	I _{B1} = -I _{B2} = 0.4A	0.8	μs

THERMAL CHARACTERISTICS

Test Conditions	Max.	Unit
R _{θJ-C} Thermal Resistance Junction to Case	1.4	°C/W

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